

Demonstration of a high efficiency nonuniform monolithic gallium-nitride distributed amplifier

S. Lee, B. Green, K. Chu, K.J. Webb and L.F. Eastman. "Demonstration of a high efficiency nonuniform monolithic gallium-nitride distributed amplifier." 2000 MTT-S International Microwave Symposium Digest 00.1 (2000 Vol. 1 [MWSYM]): 549-552.

A monolithic gallium-nitride (GaN) dual-gate HEMT distributed amplifier has been designed which offers increased efficiency by removal of the drain line dummy load. This amplifier uses a dual-gate cascode gain cell to provide higher gain and power with a wideband frequency response. A fabricated four-stage nonuniform distributed amplifier has validated this approach.

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